

### Description

The MMBF0201NL uses advanced trench technology to provide excellent  $R_{DS(ON)}$ , low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a Battery protection or in other Switching application.

## **General Features**

 $V_{DS} = 20V I_D = 2.3 A$  $R_{DS(ON)} < 60 m \Omega @ V_{GS} = 4.5 V$ 

## Application

Battery protection Load switch Uninterruptible power supply

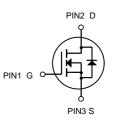
#### Package Marking and Ordering Information

Product ID	Pack	Brand	Qty(PCS)
MMBF0201NL	SOT-23	HXY MOSFET	3000

## Absolute Maximum Ratings (T<sub>A</sub>=25<sup>°</sup>C unless otherwise noted)

Parameter	Limit	Unit
Drain-Source Voltage	20	V
Gate-Source Voltage	±12	V
Drain Current-Continuous	2.3	A
Drain Current-Pulsed (Note 1)	16	A
Maximum Power Dissipation	0.9	W
Operating Junction and Storage Temperature Range	-55 To 150	°C
Thermal Resistance, Junction-to-Ambient (Note 2)	139	°C/W
	Drain-Source Voltage         Gate-Source Voltage         Drain Current-Continuous         Drain Current-Pulsed (Note 1)         Maximum Power Dissipation         Operating Junction and Storage Temperature Range	Drain-Source Voltage20Gate-Source Voltage±12Drain Current-Continuous2.3Drain Current-Pulsed (Note 1)16Maximum Power Dissipation0.9Operating Junction and Storage Temperature Range-55 To 150





N-Channel MOSFET



### Electrical Characteristics (T<sub>A</sub>=25<sup>°</sup>C unless otherwise noted)

Parameter	Symbol	ol Condition		Тур	Мах	Unit
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V Ι <sub>D</sub> =250μΑ	20	22	-	V
Zero Gate Voltage Drain Current	IDSS	V <sub>DS</sub> =20V,V <sub>GS</sub> =0V	-	-	1	μA
Gate-Body Leakage Current	lgss	V <sub>GS</sub> =±12V,V <sub>DS</sub> =0V	-	-	±100	nA
Gate Threshold Voltage	VGS(th)	V <sub>DS</sub> =V <sub>GS</sub> ,I <sub>D</sub> =250µA	0.5	0.75	1.2	V
	_	$V_{GS}$ =2.5V, I <sub>D</sub> =2.0A	-	54	72	mΩ
Drain-Source On-State Resistance	Rds(on)	V <sub>GS</sub> =4.5V, I <sub>D</sub> =2.3A	-	48	60	mΩ
Forward Transconductance	<b>g</b> fs	V <sub>DS</sub> =5V,I <sub>D</sub> =2.3A	-	8	-	S
Input Capacitance	C <sub>lss</sub>		-	260	-	PF
Output Capacitance	Coss	V <sub>DS</sub> =10V,V <sub>GS</sub> =0V,	-	48	-	PF
Reverse Transfer Capacitance	C <sub>rss</sub>	F=1.0MHz	-	27	-	PF
Turn-on Delay Time	td(on)		-	2.5	-	nS
Turn-on Rise Time	tr	V <sub>DD</sub> =10V, R <sub>L</sub> =3.3Ω	-	3.2	-	nS
Turn-Off Delay Time	td(off)	$V_{GS}$ =4.5V, $R_{GEN}$ =6 $\Omega$	-	21	-	nS
Turn-Off Fall Time	t <sub>f</sub>		-	3	-	nS
Total Gate Charge	Qg		-	2.9	5	nC
Gate-Source Charge	Q <sub>gs</sub>	V <sub>DS</sub> =10V,I <sub>D</sub> =2.3A,	-	0.4	-	nC
Gate-Drain Charge	Q <sub>gd</sub>	V <sub>GS</sub> =4.5V	-	0.6	-	nC
Diode Forward Voltage (Note 3)	Vsd	V <sub>GS</sub> =0V,I <sub>S</sub> =2.3A	-	0.75	1.2	V
Diode Forward Current (Note 2)	ls		-	-	3.3	Α

#### Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.

**2.** Surface Mounted on FR4 Board,  $t \le 10$  sec.

**3.** Pulse Test: Pulse Width  $\leq$  300µs, Duty Cycle  $\leq$  2%.

4. Guaranteed by design, not subject to production



# **Typical Electrical and Thermal Characteristics**

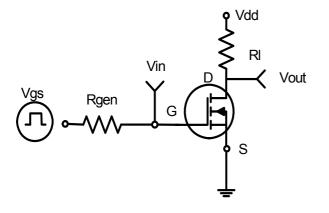
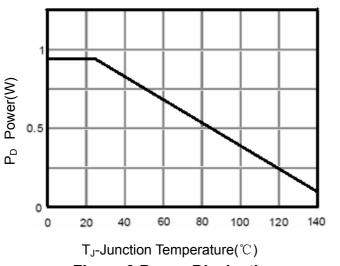
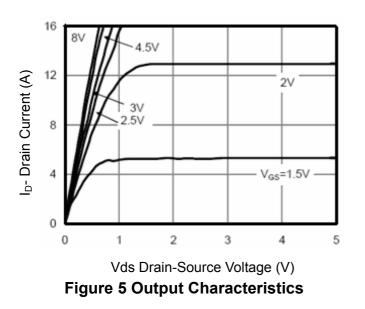
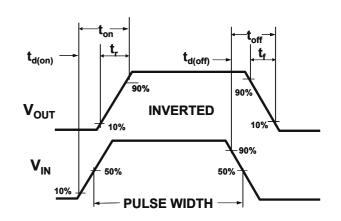


Figure 1:Switching Test Circuit

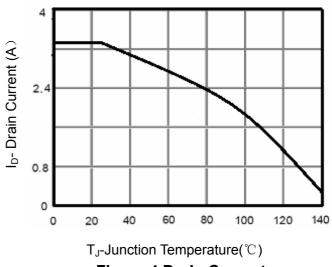


**Figure 3 Power Dissipation** 









**Figure 4 Drain Current** 

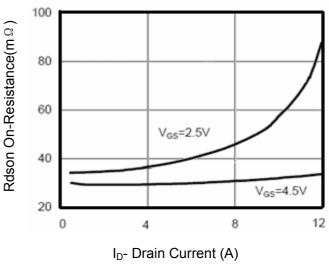
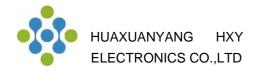
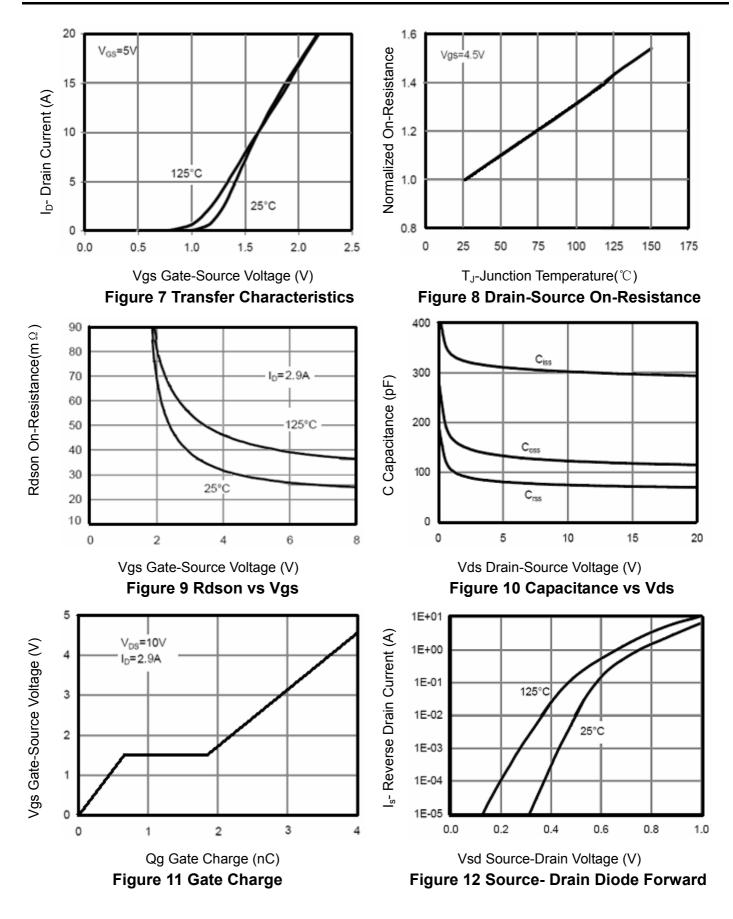


Figure 6 Drain-Source On-Resistance

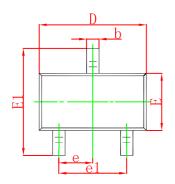


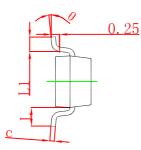
# MMBF0201NL N-Channel Enhancement Mode MOSFET

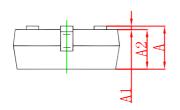




## **SOT-23 Package Outline Dimensions**

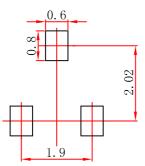






Symbol	Dimensions In Millimeters		Dimensions In Inches		
	Min	Max	Min	Max	
Α	0.900	1.150	0.035	0.045	
A1	0.000	0.100	0.000	0.004	
A2	0.900	1.050	0.035	0.041	
b	0.300	0.500	0.012	0.020	
С	0.080	0.150	0.003	0.006	
D	2.800	3.000	0.110	0.118	
Е	1.200	1.400	0.047	0.055	
E1	2.250	2.550	0.089	0.100	
e	0.950 TYP		0.037 TYP		
e1	1.800	2.000	0.071	0.079	
L	0.550 REF		0.022 REF		
L1	0.300	0.500	0.012	0.020	
θ	0°	8°	0°	8°	

## SOT-23 Suggested Pad Layout



Note: 1.Controlling dimension:in millimeters.

2.General tolerance:± 0.05mm.
 3.The pad layout is for reference purposes only.



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give rise to accidents or events that could endanger numan lives, that could give rise to smoke or fire, or that could cause damage to other property. When designing equipment, adopt safety measures so that these kinds of accidents or events cannot occur. Such measures include but are not limited to protective circuits and error prevention circuits for safe design, redundant design, and structural design.

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